

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	353	(etchant or slurry) same tub\$4 same (CMP or "chemical mechanical polishing")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 08:49
L2	3297	(etchant or slurry) and (tub\$4 or nozzle or inlet) and (CMP or "chemical mechanical polishing") and (wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 08:51
L3	353	(etchant or slurry) same (tub\$4 or nozzle or inlet) same (CMP or "chemical mechanical polishing") same (wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 08:52
L4	3827	(etchant or slurry) same remov\$4 same suction\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 08:53
L5	161	4 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 08:56
L8	1422	(etchant or slurry or solution) same (nozzle or inlet or tube) same wafer same (rins\$3 or wash\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 08:56
L10	766	8 and semiconductor and clean\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 08:59
L11	3	"5722875".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/08 09:02